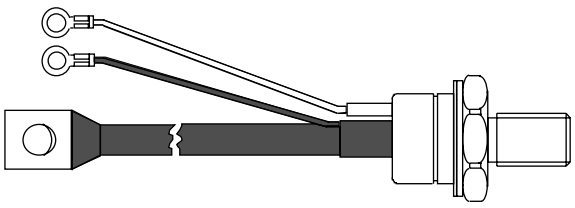
Phase Control Thyristors (Stud Version), 110 A



TO-209AC (TO-94)

FEATURES

- High current and high surge ratings
- Hermetic ceramic housing
- RoHS compliant
- Lead (Pb)-free
- Designed and qualified for industrial level

RoHS COMPLIANT

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

PRODUCT SUMMARY	
$I_{T(AV)}$	110 A

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		110	A
	T_C	90	°C
$I_{T(RMS)}$		172	A
I_{TSM}	50 Hz	2080	
	60 Hz	2180	
I^2t	50 Hz	21.7	kA^2s
	60 Hz	19.8	
V_{DRM}/V_{RRM}		400 to 1200	V
t_q	Typical	110	µs
T_J		- 40 to 140	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM}, MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM}, MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
110RKI 111RKI	40	400	500	20
	80	800	900	
	120	1200	1300	

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave			110	A
					90	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 83 °C case temperature			172	A
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	2080	
		t = 8.3 ms			2180	
		t = 10 ms	100 % V_{RRM} reapplied		1750	
		t = 8.3 ms			1830	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied		21.7	kA^2s
		t = 8.3 ms			19.8	
		t = 10 ms	100 % V_{RRM} reapplied		15.3	
		t = 8.3 ms			14.0	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied			217	$kA^2\sqrt{s}$
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.82	V
High level value of threshold voltage	$V_{T(TO)2}$	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			1.02	
Low level value of on-state slope resistance	r_{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			2.16	mΩ
High level value of on-state slope resistance	r_{t2}	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			1.70	
Maximum on-state voltage	V_{TM}	I_{pk} = 350 A, $T_J = T_J$ maximum, t_p = 10 ms sine pulse			1.57	V
Maximum holding current	I_H	T_J = 25 °C, anode supply 6 V resistive load			200	mA
Typical latching current	I_L				400	

SWITCHING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dI/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1$ µs $T_J = T_J$ maximum, anode voltage ≤ 80 % V_{DRM}	300	A/µs
Typical delay time	t_d	Gate current 1 A, dI_g/dt = 1 A/µs V_d = 0.67 % V_{DRM}, T_J = 25 °C	1	µs
Typical turn-off time	t_q	I_{TM} = 50 A, $T_J = T_J$ maximum, dI/dt = - 5 A/µs V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 25 Ω	110	

BLOCKING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I_{RRM}, I_{DRM}	$T_J = T_J$ maximum rated V_{DRM}/V_{RRM} applied	20	mA

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES TYP.	VALUES MAX.	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		12		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, f = 50 Hz, d% = 50		3.0		W
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		3.0		A
Maximum peak positive gate voltage	$+ V_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms		20		V
Maximum peak negative gate voltage	$- V_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms		10		V
DC gate current required to trigger	I_{GT}	T_J = - 40 °C	Maximum required gate trigger/current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	180	-	mA
		T_J = 25 °C		80	120	mA
		T_J = 140 °C		40	-	mA
DC gate voltage required to trigger	V_{GT}	T_J = - 40 °C		2.5	-	V
		T_J = 25 °C		1.6	2	V
		T_J = 140 °C		1	-	V
DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V_{DRM} anode to cathode applied	6.0		mA
DC gate voltage not to trigger	V_{GD}	$T_J = T_J$ maximum		0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	T_J		- 40 to 140	°C
Maximum storage temperature range	T_{Stg}		- 40 to 150	°C
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	0.27	K/W
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth, flat and greased	0.1	K/W
Mounting torque, ± 10 %		Non-lubricated threads	15.5 (137)	N · m (lbf · in)
		Lubricated threads	14 (120)	N · m (lbf · in)
Approximate weight			130	g
Case style		See dimensions - link at the end of datasheet	TO-209AC (TO-94)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.043	0.031	$T_J = T_J$ maximum	K/W
120°	0.052	0.053		K/W
90°	0.066	0.071		K/W
60°	0.096	0.101		K/W
30°	0.167	0.169		K/W

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

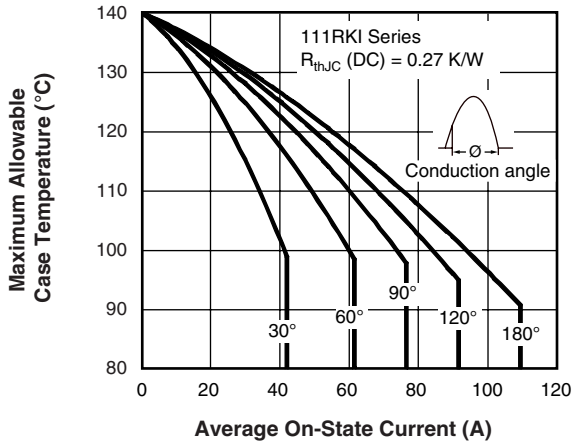


Fig. 1 - Current Ratings Characteristics

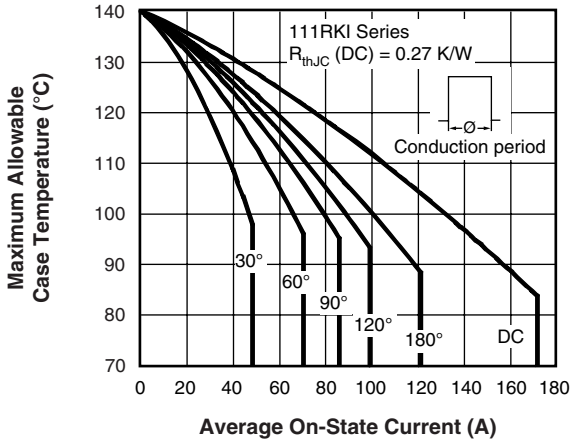
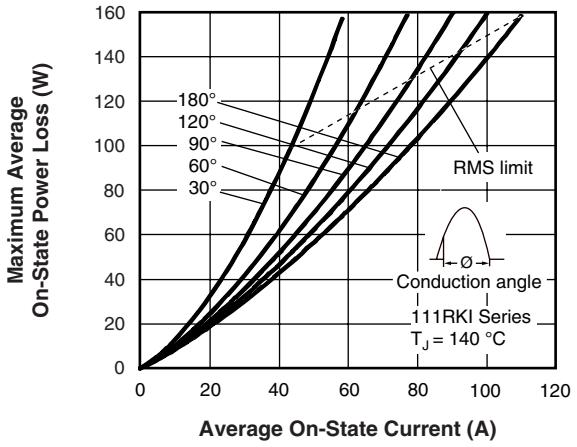


Fig. 2 - Current Ratings Characteristics



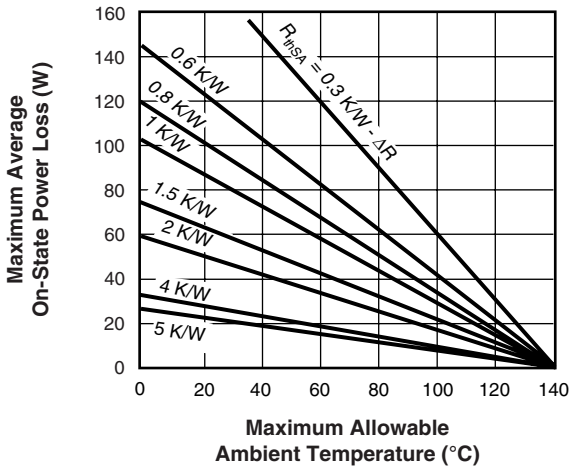
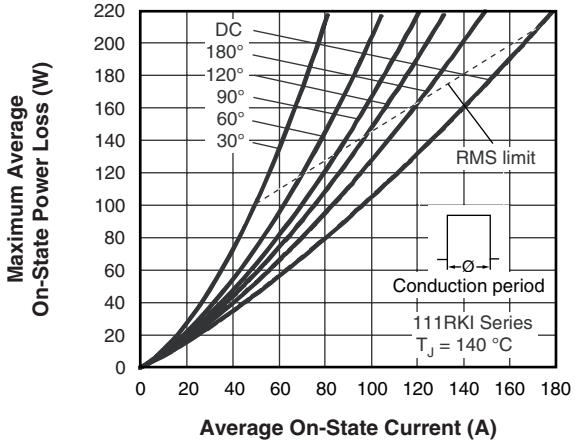


Fig. 3 - On-State Power Loss Characteristics



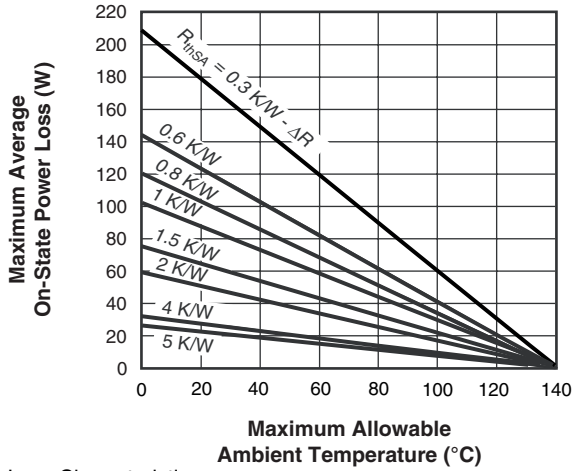


Fig. 4 - On-State Power Loss Characteristics

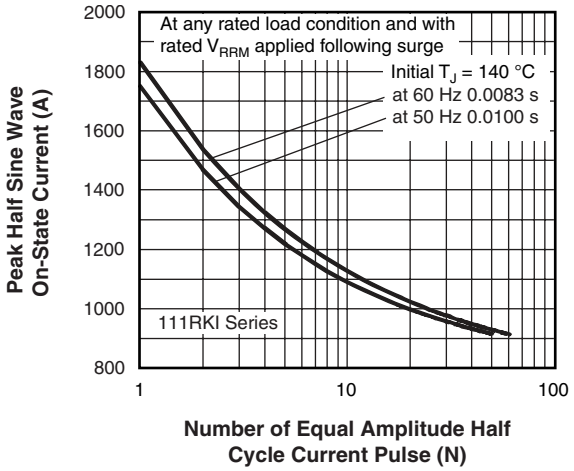


Fig. 5 - Maximum Non-Repetitive Surge Current

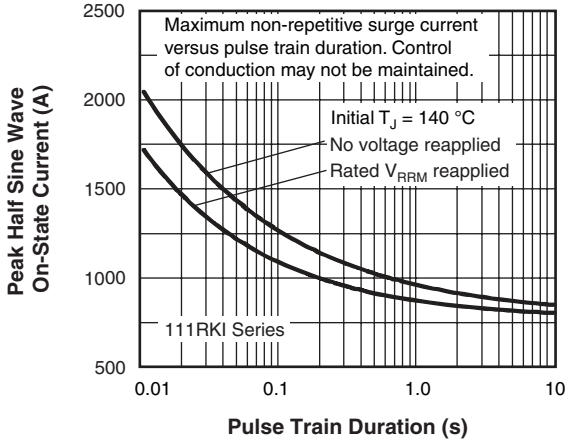


Fig. 6 - Maximum Non-Repetitive Surge Current

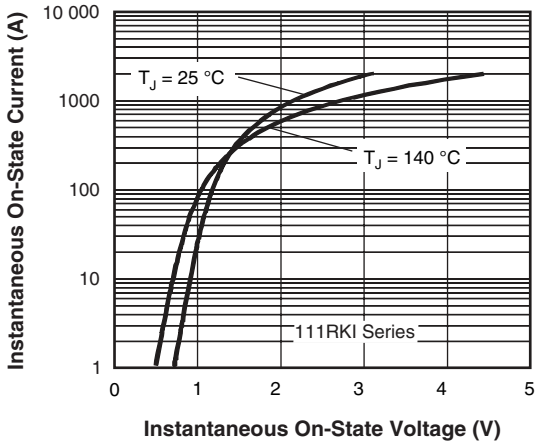


Fig. 7 - On-State Voltage Drop Characteristics

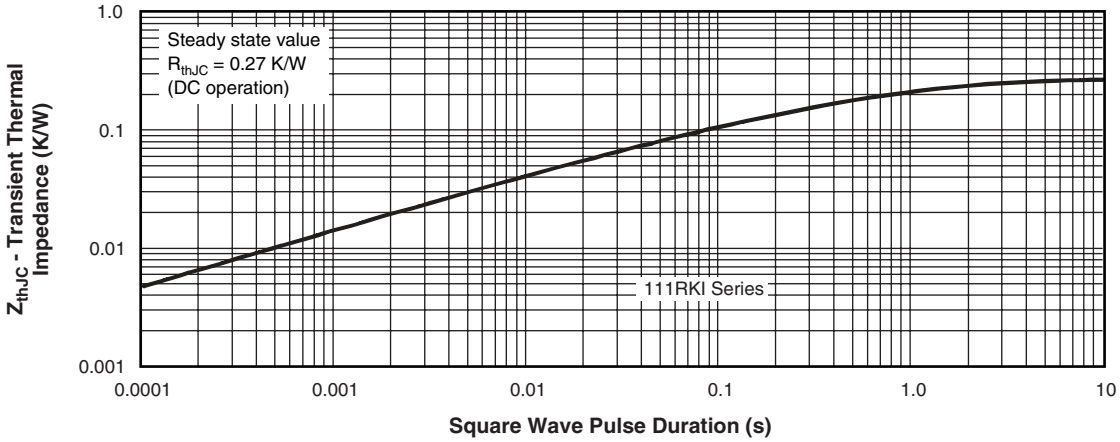


Fig. 8 - Thermal Impedance Z_{thJC} Characteristic

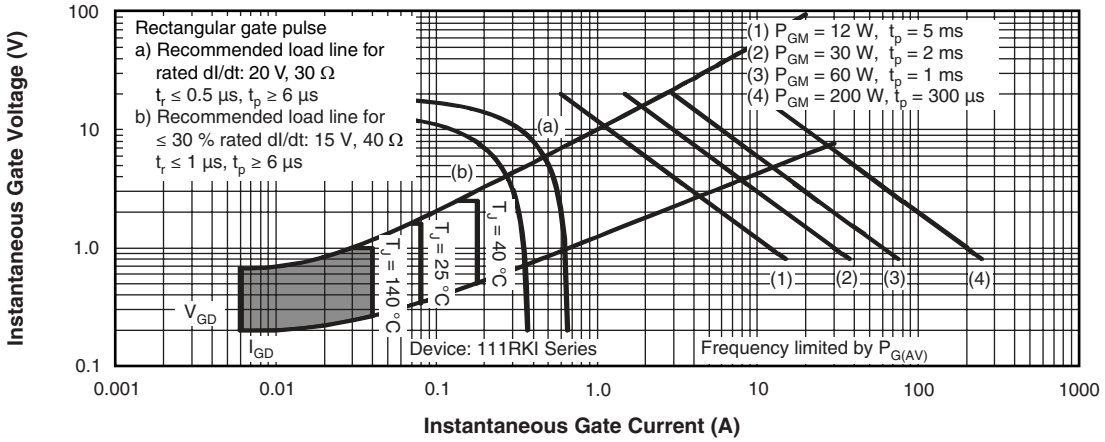


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code

11	0	RKI	120	PbF
1	2	3	4	5

- 1 - $I_{T(AV)}$ rated average output current (rounded/10)
- 2 - 0 = Eyelet terminals (gate and auxiliary cathode leads)
  1 = Fast-on terminals (gate and auxiliary cathode leads)
- 3 - Thyristor
- 4 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 5 - Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95003

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